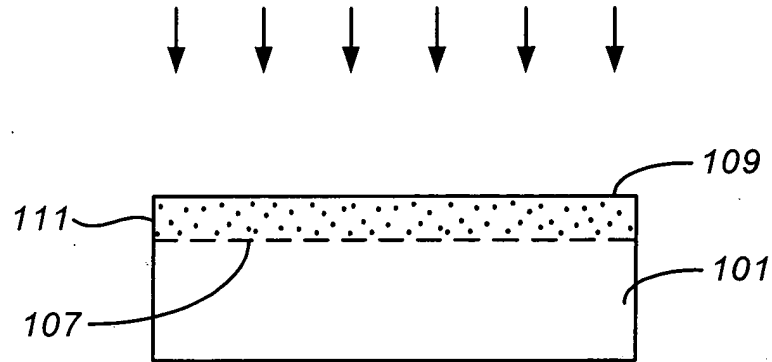




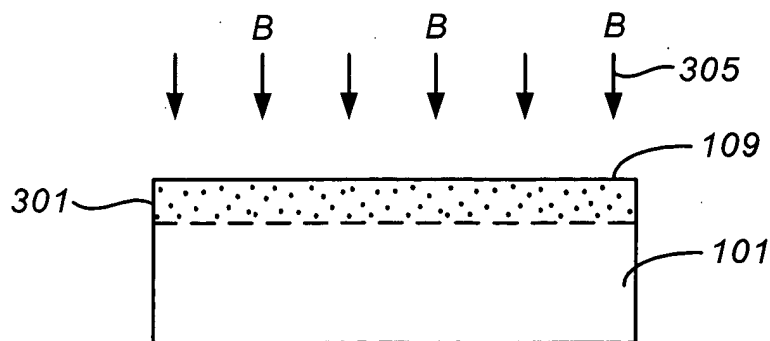
1/6



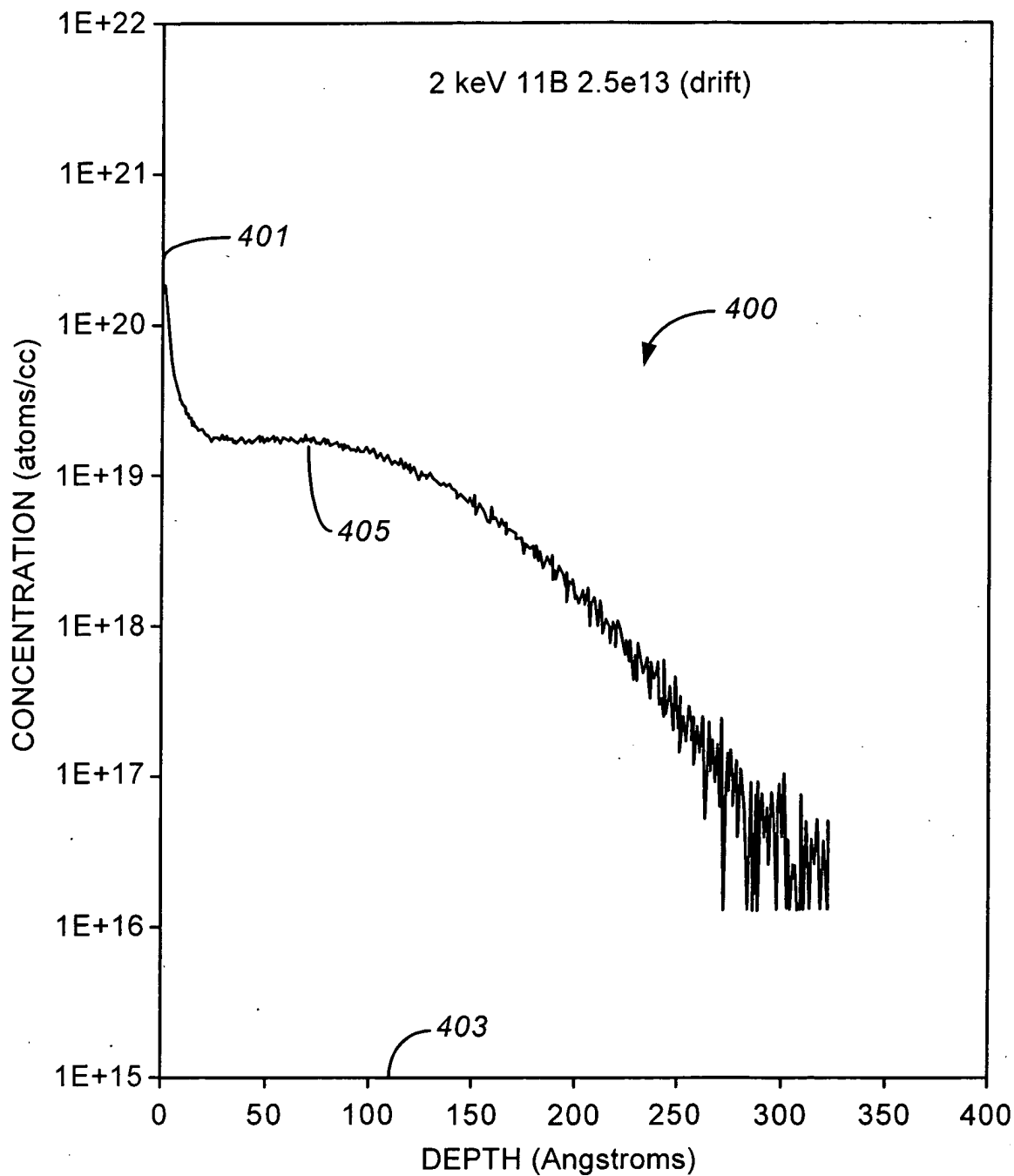
**FIG. 1**



**FIG. 2**

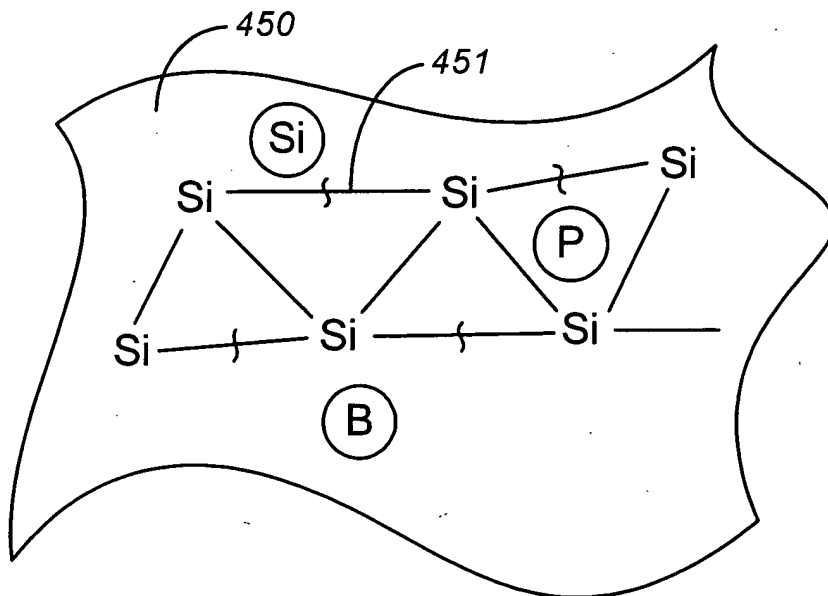


**FIG. 3**

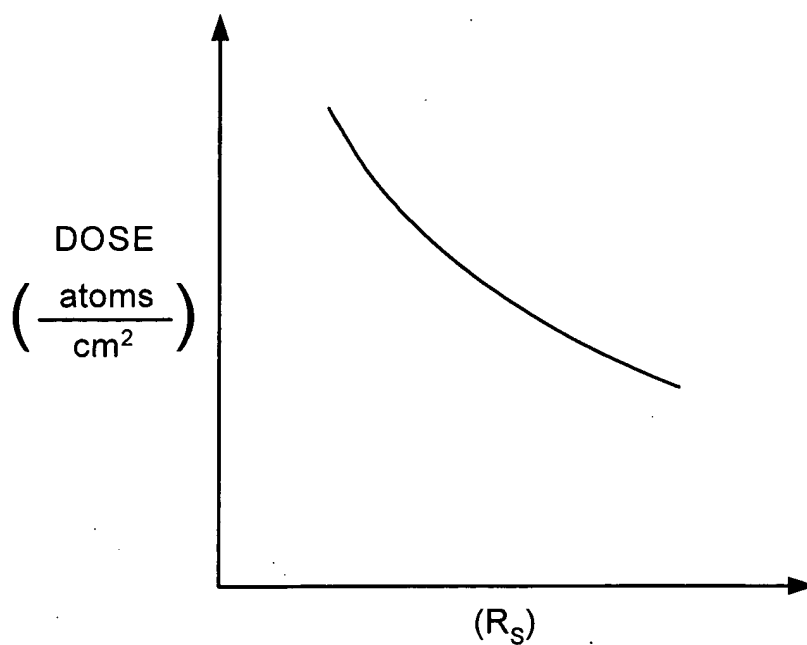


**FIG. 4**

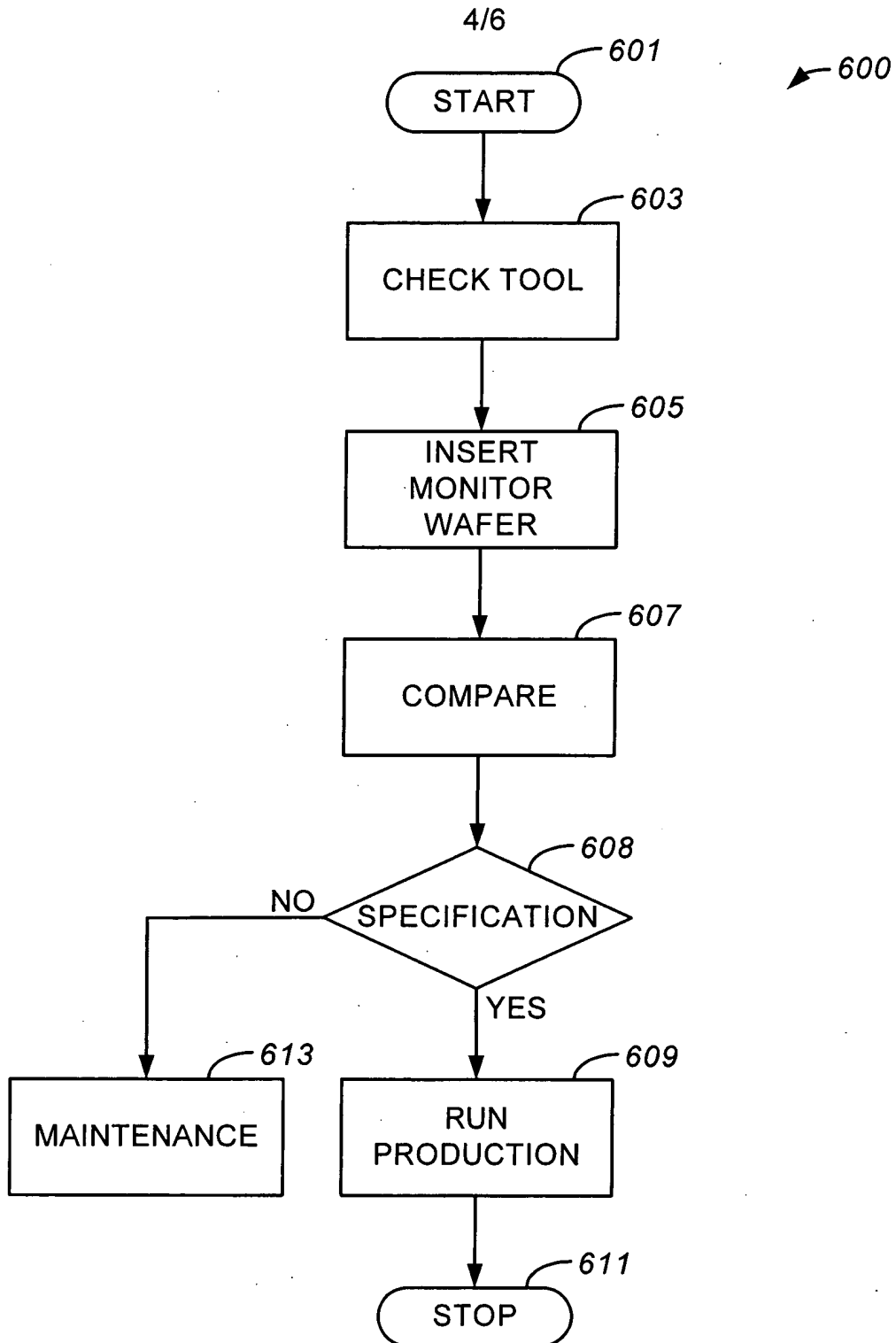
3/6



**FIG. 4A**

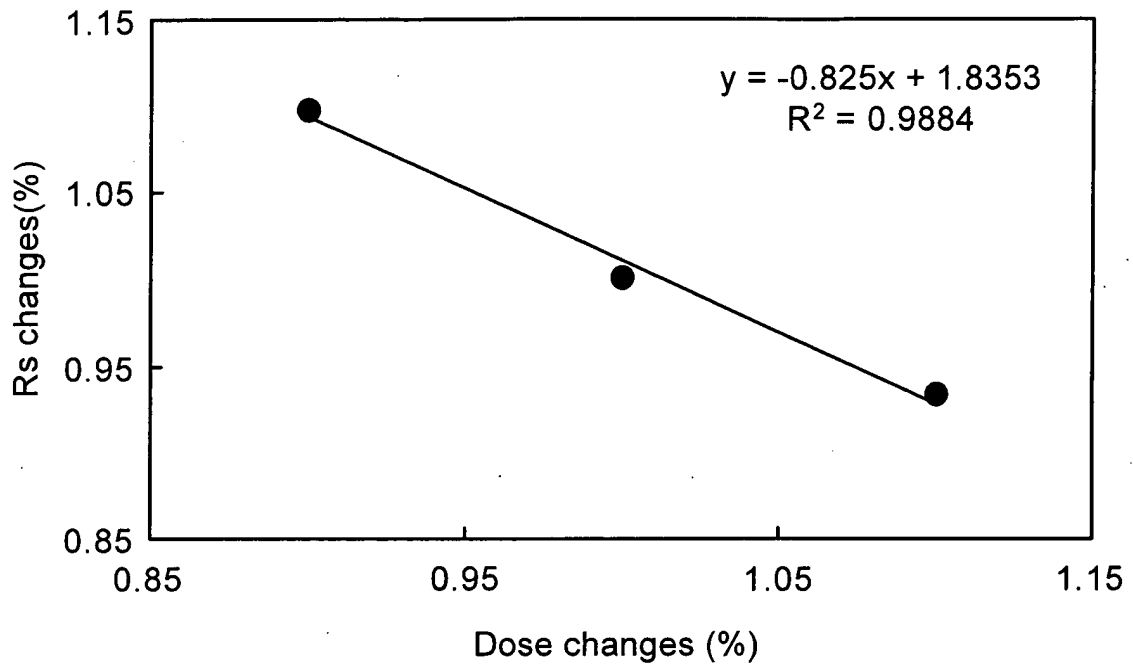


**FIG. 5**

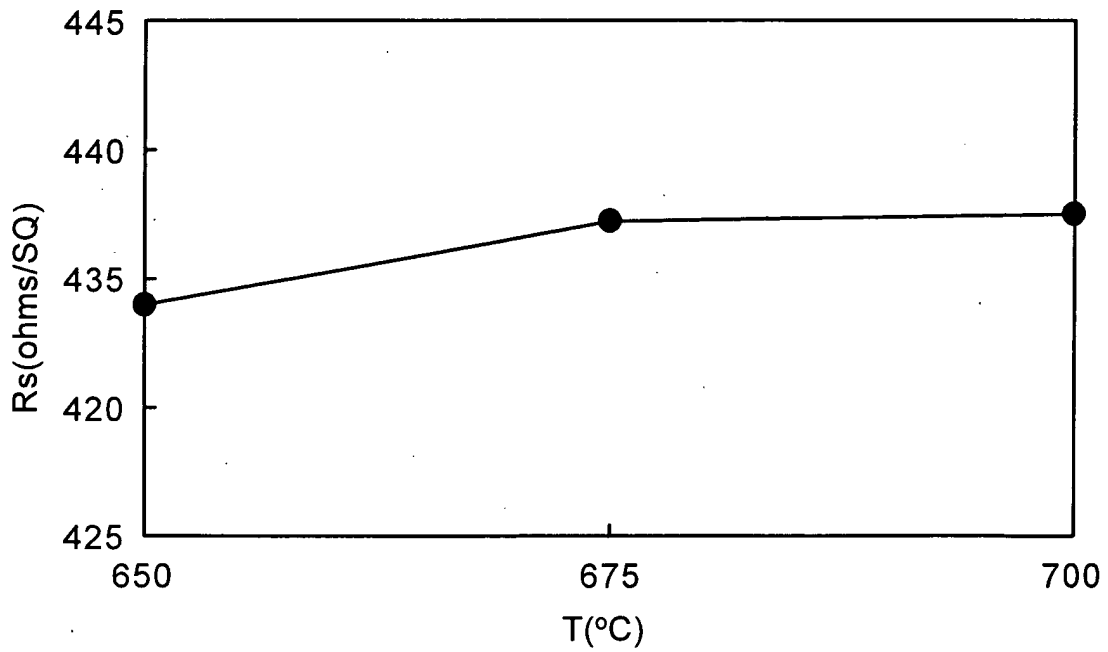


**FIG. 6**

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**FIG. 7**



**FIG. 8**

**Table 1** The effect of silicon implantation on Boron activation.  
 Implantation conditions: Silicon/20KeV/1E15 before Boron/2KeV/4E14;  
 annealing conditions: 700°C, 30 seconds, N<sub>2</sub> as annealing ambient

	Implantation	Annealing	Rs/Uniformity(%)
Implanted with both Si and B	Si/20K/1E15/T07+ B/2K40E4/T00	T0700RTA30S	442.72/0.329%
Implanted with B only	B/2K/40E4/T00		7940.3/1.352%

**FIG. 9**